Supporting information of

Homogenizing Liquid-like Cu Sublattice for High-performance

Cu₂Te_{0.5}Se_{0.5} Thermoelectric Materials

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4. References

1. Details in the Theoretical Calculations

1.1 Lorenz number¹

The total thermal conductivity κ_{tot} is divided into electrical (κ_{ele}) and lattice thermal conductivity (κ_{lat}), the subtraction of κ_{ele} from κ_{tot} is calculated by Wiedeman-Franz relation $\kappa_{lat} = \kappa_{tot} - \kappa_{ele}$ ($\kappa_{ele} = L \cdot \sigma \cdot T$), where σ and L is electrical conductivity and Lorenz number, respectively. L was calculated according to the equation (S1 – S3).

$$L = \left(\frac{k_B}{e}\right)^2 \left[\frac{3F_0(\eta)F_2(\eta) - 4F_1(\eta)^2}{F_0(\eta)^2}\right]$$
(S1)

$$S = \pm \frac{k_B}{e} (\frac{2F_1(\eta)}{F_0(\eta)} - \eta)$$
(S2)

$$F_n(\eta) = \int_0^\infty \frac{\chi^n}{1 + e^{\chi - \eta}} d\chi$$
(S3)

where S is the Seebeck coefficient, $F_n(\eta)$ is the *n*th order Fermi integral, η is the reduced Fermi energy, *e* is the charge of an electron, and k_B is the Boltzmann constant.

1.2 Weighted mobility²

To evaluate the manufacturing of engineering semiconductor devices, the understanding of the charge carrier mobility is required. At room temperature and above, and for mobilities as low as 10^{-3} cm²·V⁻¹·s⁻¹, the weighted mobility μ_w can be calculated from the Seebeck coefficient and electrical resistivity measurements according to the equation (S4).

$$\mu_{w} = 331 \frac{cm^{2}}{Vs} \left(\frac{m\Omega \ cm}{\rho}\right) \left(\frac{T}{300 \ K}\right)^{-3/2} \left[\frac{exp\left[\frac{|S|}{\kappa_{B}/e} - 2\right]}{1 + exp\left[-5\left(\frac{|S|}{\kappa_{B}/e} - 1\right)\right]} + \frac{\frac{3 \ |S|}{\pi^{2}\kappa_{B}/e}}{1 + exp\left[5\left(\frac{|S|}{\kappa_{B}/e} - 1\right)\right]}\right]$$

(S4)

where ρ is the electrical resistivity measured in m $\Omega \cdot \text{cm}$, *T* is the absolute temperature in K, S is the Seebeck coefficient, and $\kappa_{\text{B}}/e = 86.3 \,\mu\text{V}\cdot\text{K}^{-1}$.

1.3 Theoretical lattice thermal conductivity ³

The minimum limit of the theoretical lattice thermal conductivity (κ_{min}) was estimated to be based on Cahill's formulation

$$\kappa_{min} = \left(\frac{\pi}{6}\right)^{1/3} k_B n^{2/3} \sum_i \nu_i \left(\frac{T}{\Theta_i}\right)^2 \int_0^{\Theta_i/T} \frac{x^3 e^x}{(e^x - 1)^2} dx$$
(S5)

The sum is taken over the three sound modes (two transverse and one longitudinal) with speeds of sound v_i , Θ_i is the cutoff frequency for each polarization expressed in degress K, $\Theta_i = v_i (\hbar/k_B) (6\pi^2 n)^{1/3}$, and *n* is number density of atoms.

2. Supporting Table

Table S1. Density of the Quench at liquid, Quench at cubic, and Quench at trigonal samples after SPS process.

Samples	Density (g cm ⁻³)	Relative density (%)
Quench at liquid	7.41	99.65
Quench at cubic	7.46	98.89
Quench at trigonal	7.48	98.72

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Figure S4. The stability of the Cu₂Te_{0.5}Se_{0.5} samples of Quench at liquid was tested for 5 cycles for temperature-dependent (a) electrical conductivity (σ), (b) Seebeck coefficient (*S*), and (c) power factor (PF)

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